



DMN3018SFG

30V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = +25°C		
30V	$21m\Omega$ @ V_{GS} = $10V$	8.5A		
30 V	$35m\Omega$ @ $V_{GS} = 4.5V$	6.6A		

Description

This MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Backlighting
- Power Management Functions
- DC-DC Converters

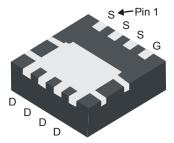
Features and Benefits

- Low R_{DS(ON)} ensures on state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 standards for High Reliability

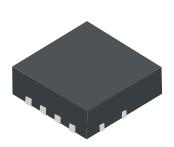
Mechanical Data

- Case: POWERDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.072 grams (approximate)

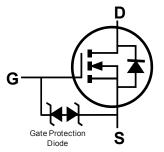








Top View



Top View Internal Schematic

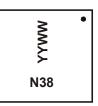
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3018SFG-7	POWERDI®3333-8	2000/Tape & Reel
DMN3018SFG-13	POWERDI®3333-8	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



N38 = Product Type Marking Code YYWW = Date Code Marking YY = Last digit of year (ex: 11 = 2011) WW = Week code (01 ~ 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	±25	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	Ι _D	8.5 6.8	А
	t<10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	Ι _D	11.3 9.1	Α
Continuous Prain Current (Note 6) // - 4 5\/	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	6.6 5.3	Α
Continuous Drain Current (Note 6) V _{GS} = 4.5V	t<10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	8.7 7.0	Α
Maximum Continuous Body Diode Forward Current	I _S	2.5	Α		
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I _{DM}	60	Α
Avalanche Current (Note 7) L = 0.1mH			I _{AS}	18	Α
Avalanche Energy (Note 7) L = 0.1mH			E _{AS}	16	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Units	
Total Power Dissipation (Note 5)		P_{D}	1.0	W	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	0	126	°C/W	
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{\theta JA}$	71	- C/VV	
Total Power Dissipation (Note 6)		P_{D}	2.2	W	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State		56	°C/W	
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{\theta JA}$	31		
Thermal Resistance, Junction to Case		$R_{ heta JC}$	7.0		
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-55 to 150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	V _{DS} = 24V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	±10	μA	V _{GS} = ±20V, V _{DS} = 0V	
ON CHARACTERISTICS (Note 7)			-				
Gate Threshold Voltage	V _{GS(th)}	1	1.7	2.1	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance		_	16	21	mΩ	$V_{GS} = 10V, I_D = 10A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	21	35	11122	$V_{GS} = 4.5V, I_D = 8.5A$	
Diode Forward Voltage	V _{SD}	0.5	_	1.2	V	V _{GS} = 0V, I _S = 1A	
DYNAMIC CHARACTERISTICS (Note 8)			-				
Input Capacitance	C _{iss}	-	697	_	рF	\\ 45\\\\\ 0\\	
Output Capacitance	Coss	_	97	_	pF	$V_{DS} = 15V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	67	_	pF		
Gate resistance	Rg	_	1.47	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Q_{g}	_	6.0	_	nC		
Total Gate Charge (V _{GS} = 10V)	Qq	_	13.2	_	nC	V _{GS} = 10V, V _{DS} = 15V,	
Gate-Source Charge	Q _{gs}	_	2.2	_	nC	I _D = 9A	
Gate-Drain Charge	Q _{qd}	_	1.8	_	nC	1	
Turn-On Delay Time	t _{D(on)}	_	4.3	_	ns		
Turn-On Rise Time	t _r	_	4.4	_	ns	V_{DD} = 15V, V_{GS} = 10V, R_{L} = 15 Ω , I_{D} = 1A, R_{G} = 6 Ω	
Turn-Off Delay Time	t _{D(off)}		20.1	_	ns		
Turn-Off Fall Time	t _f		4.1	_	ns		
Reverse Recovery Time	T _{rr}		7.3	_	ns	L 04 didt 5004/c-	
Reverse Recovery Charge	Q _{rr}	_	7.9	_	$_{\rm nC}$ $_{\rm l_F}$ = 9A, di/dt = 500A/ μ s		

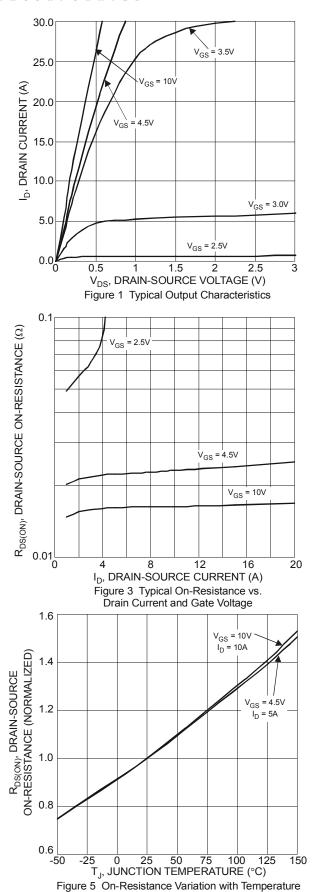
5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate

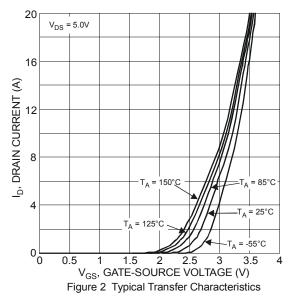
7. I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C

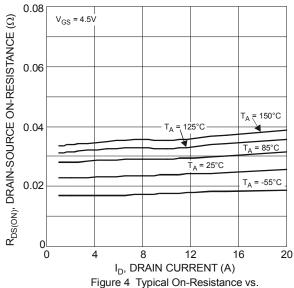
8. Short duration pulse test used to minimize self-heating effect.

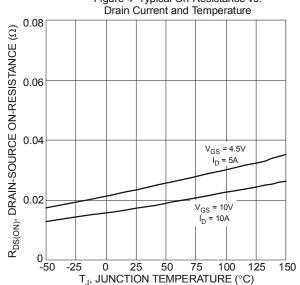
9. Guaranteed by design. Not subject to product testing.















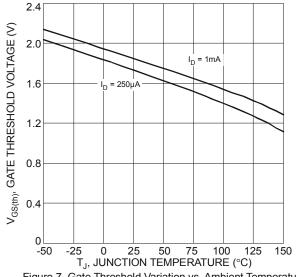
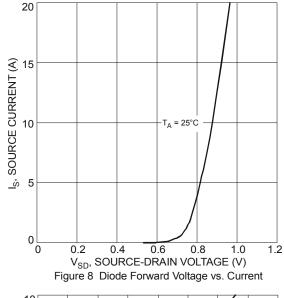


Figure 7 Gate Threshold Variation vs. Ambient Temperature



10 $V_{\rm GS}$ GATE THRESHOLD VOLTAGE (V) $V_{DS} = 15V$ 8 I_D = 9A 6 4 2

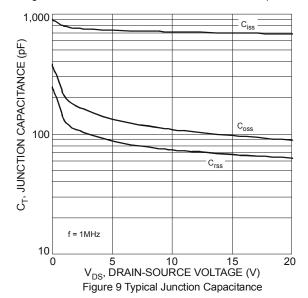
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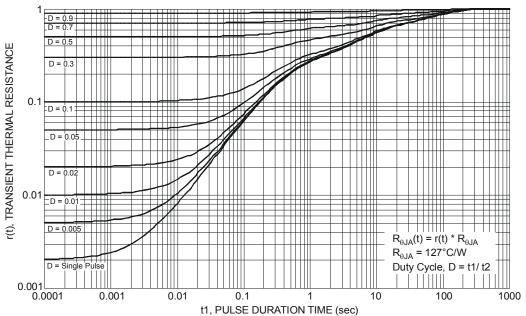
 $\boldsymbol{Q}_{g},$ TOTAL GATE CHARGE (nC)

Figure 10 Gate Charge

12

16





0

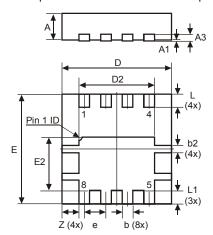
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Package Outline Dimensions

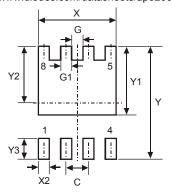
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



POWERDI®3333-8					
Dim	Min Max		Тур		
D	3.25	3.35	3.30		
П	3.25	3.35	3.30		
D2	2.22	2.32	2.27		
E2	1.56	1.66	1.61		
Α	0.75	0.85	0.80		
A 1	0	0.05	0.02		
Α3	-	-	0.203		
q	0.27	0.37	0.32		
b2	1	-	0.20		
L	0.35	0.45	0.40		
L1	_	_	0.39		
е	_	_	0.65		
Z	_	-	0.515		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)			
С	0.650			
G	0.230			
G1	0.420			
Y	3.700			
Y1	2.250			
Y2	1.850			
Y3	0.700			
X	2.370			
X2	0.420			



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